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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

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In re Patent Application of

TAKAHASHI et al

Atty. Ref.: 829-585

Serial No. to be assigned

Group: unknown

Filed: September 18, 2001

Examiner: unknown

For: Crystal Growth Method, Production Method of Semiconductor Microstructure,
Semiconductor Device, and System

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Assistant Commissioner for Patents
Washington, DC 20231

Sir:

PRELIMINARY AMENDMENT

In order to place the above-identified application in better condition for
examination, please amend the application as follows:

IN THE CLAIMS

Cancel claims 1-28 and substitute therefore new claims 1-113 appearing on the
attached pages 1-25.

REMARKS

Entry of new claims 1-113 is respectfully requested.

Respectfully submitted,

NIXON & VANDERHYE P.C.

September 18, 2001

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